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A Machine Learning Framework for NAND Flash Lifetime Extension

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A World of Machines... Learning

In the last few years, machine learning has become ubiquitous

Machine Learning

Deep Learning

- Machine vision
- Object detection

• ...



Data Analysis

- Time series analysis
- Regression
- ...



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- Time series analysisRegression
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The common approach today is: Do you have a problem? Fix it with Machine Learning!



The "Devil" in Machine Learning

Using machine learning is not as simple as it appears...

- One of the biggest problems when using machine learning is neither the algorithm nor the implementation...
- "The problem is not the problem. The problem is how you define the problem..."



NAND Flash Memories Today

- 3D up to 96 layers
- 8 Tbits in a single BGA package
- Quad level cell (QLC)
- Circuits under array
- I/O bus @ 1200 MT/s
- tPROG ≈ 3 ms
- tREAD ≈ 100 µs
- tERASE ≈ 10 ms
- Cost per Gb ≈ HDD



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Reliability!! NAND FER fighting against the Shannon limit



- The higher the data reliability, the longer the device's lifetime (and the cheaper the solution...)
- Problem statement: increase data reliability to extend NAND flash's lifetime

...Now what?...



3D NAND Flash Memories

Having a deep understanding of the device's physics is the only way to get good data reliability

- 3D NAND flash is a stack of multiple memories
- Array architecture
- Cell-to-cell variability

Gate (CGs) Selectors Source Line Source Line (BLS's) Selector (SLS) Channel (CH) Bitline (BL) Bitline Gate (CGs) (CH) Source Line Selecto Source Line (SL) ine (SI) (SLS)

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"....Welcome to the jungle..."

Many parameters impact NAND flash reliability including soft info, code-rate, cycling speed, and temperature.

- Too many parameters to look at
- Too many possible correlations
- Too many features

There is no guarantee that we'll find the best setting for each working conditions...



Problem? Use Machine Learning







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NAND flash know-how

Machine learning know-how

...Now what?...

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* Rino Micheloni, 3D Nand Flash Memories, Springer 2016



What do we want to achieve?

- A framework able to test which parameters impact the reliability of a NAND flash (and which parameters do not)
- An framework able to tune these parameters depending on the reliability target
- Output: An algorithm (model) able to learn how to enhance the reliability in a completely agnostic and autonomous way → Machine Learning!
- Remember, we are looking for a framework and not an algorithm! The algorithm is just the output of the framework.



Machine Learning Framework at FSPL

Characterization of NAND flash memories



- Brute force testing of thousands of different machine learning algorithms
- Create a software model of the target algorithms
- Implement best candidate
 algorithm at firmware level
- Hardware acceleration





• Test with NVMe Flashtec™ controller





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Where Are We Today?

"...a strategic inflection point is a time in the life of business when its fundamentals are about to change. That change can mean an opportunity to rise to new heights. – Andy Grove"





Conclusions: M²ZC Conjecture

"In hyperscaled NAND flash memories each layer will be optimized by machine learning"

- Takeaway #1: Does machine learning work with NAND flash memories?→ Yes!
- Takeaway #2: Are humans obsolete?

 → Don't think so! We still need to guide the machine (a student can learn at a much faster rate with a good teacher...)

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Thanks

Q&A

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